

N-channel SiC power MOSFET

V_{DSS}	1200V
R _{DS(on)} (Typ.)	160m Ω
I _D	17A
P_D	103W

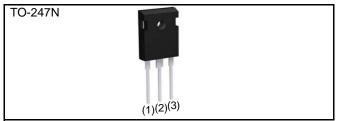
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

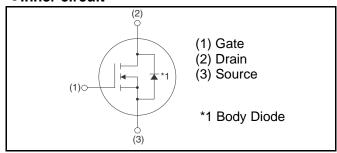
Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

Outline



●Inner circuit



Packaging specifications

		
	Packing	Tube
	Reel size (mm)	-
Type	Tape width (mm)	-
Type	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT3160KL

◆Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{ m DSS}$	1200	V	
Continuous drain current	$T_c = 25^{\circ}C$	I _D *1	17	А
Continuous drain current	$T_c = 100$ °C	I _D *1	12	А
Pulsed drain current		I _{D,pulse} *2	42	А
Gate - Source voltage		V_{GSS}	-4 to 22	V
Gate-Source Surge Voltage		V_{GSS_surge}	−4 to 22	V
Recommended Drive Voltage		V_{GS_op}	0 / 18	V
Junction temperature		T _j	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

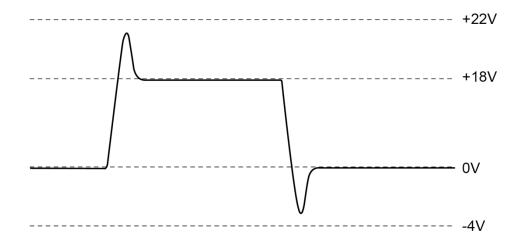
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Тур.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	1.12	1.46	°C/W

•Electrical characteristics ($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol Conditions —		Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	1200	-	-	V
		$V_{DS} = 1200V, V_{GS} = 0V$				
Zero gate voltage drain current	I _{DSS}	$T_j = 25$ °C	-	1	10	μΑ
drain barront		T _j = 150°C	-	2	-	
Gate - Source leakage current	I_{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS} _	$V_{GS} = -4V$, $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_{D} = 2.5 \text{mA}$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 5A$				
Static drain - source on - state resistance	R _{DS(on)} *3	$T_j = 25$ °C	-	160	208	mΩ
		T _j = 125°C	-	240	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	18	-	Ω

●Example of acceptable Vgs waveform



●Electrical characteristics (T_a = 25°C)

Darameter	Cumbal	Symbol Conditions -		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g _{fs} *3	$V_{DS} = 10V, I_{D} = 5A$	-	2.5	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	398	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	41	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	18	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 600V	-	45	-	pF
Turn - on delay time	t _{d(on)} *3	$V_{DD} = 400V, I_{D} = 5A$	-	14	-	
Rise time	t _r *3	V _{GS} = 18V/0V	-	18	-	no
Turn - off delay time	t _{d(off)} *3	$R_L = 80\Omega$	-	24	-	ns
Fall time	t _f *3	$R_G = 0\Omega$	-	25	-	
Turn - on switching loss	E _{on} *3	$V_{DD} = 600V, I_{D} = 5A$ $V_{GS} = 18V/0V$	-	62	-	1
Turn - off switching loss	E _{off} *3	R _G = 0Ω L=750μH *E _{on} includes diode reverse recovery	-	12	-	μJ

● Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol Condition	Conditions	Values			Unit
		Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*3}	V _{DD} = 600V	-	42	ı	
Gate - Source charge	Q _{gs} *3	I _D = 5A	-	11	-	nC
Gate - Drain charge	Q _{gd} *3	V _{GS} = 18V	-	18	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 600V, I_D = 5A$	-	9.6	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} PW \leq 10 $\mu s,$ Duty cycle \leq 1%

^{*3} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai nietei	Symbol Conditions		Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	-T _c = 25°C	-	1	17	А
Inverse diode direct current, pulsed	I _{SM} *2		-	-	42	А
Forward voltage	V _{SD} *3	$V_{GS} = 0V, I_{S} = 5A$	-	3.2	-	V
Reverse recovery time	t _{rr} *3	I _F =5A, V _R = 600V di/dt = 1100A/μs	-	13	1	ns
Reverse recovery charge	Q _{rr} *3		-	26	-	nC
Peak reverse recovery current	I _{rrm} *3		-	4	-	Α

Fig.1 Power Dissipation Derating Curve

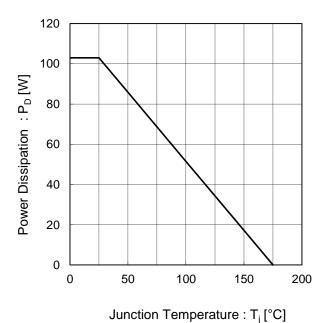
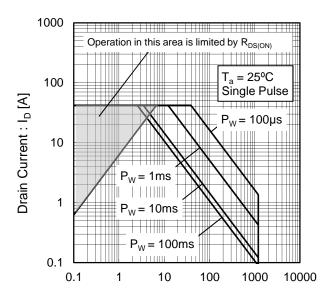
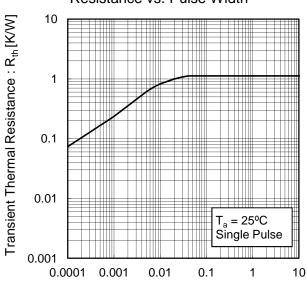


Fig.2 Maximum Safe Operating Area



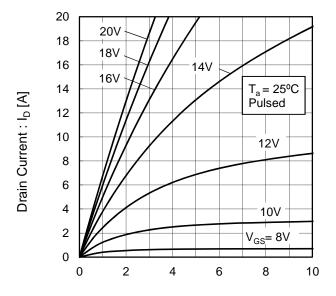
Drain - Source Voltage : V_{DS} [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



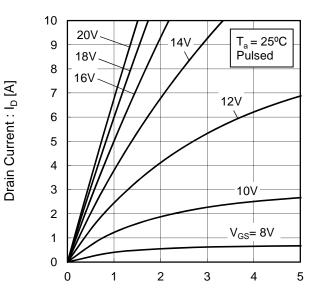
Pulse Width : P_W [s]

Fig.4 Typical Output Characteristics(I)

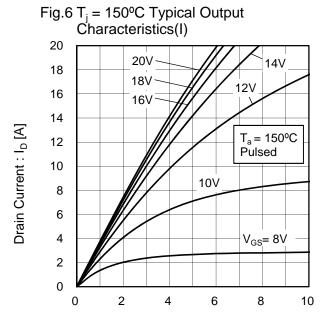


Drain - Source Voltage : V_{DS} [V]

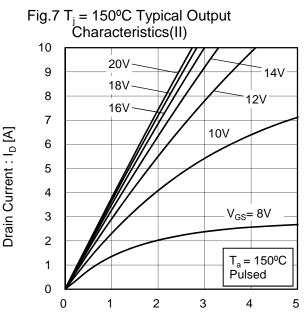
Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

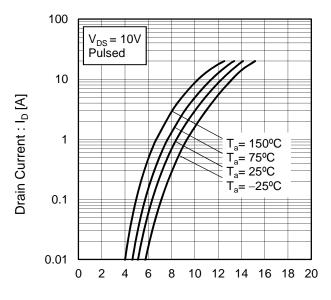


Drain - Source Voltage : V_{DS} [V]



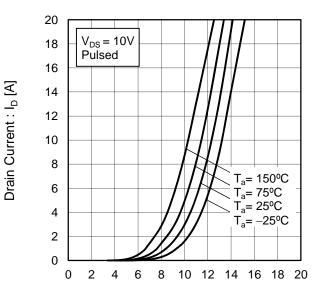
Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Transfer Characteristics (I)



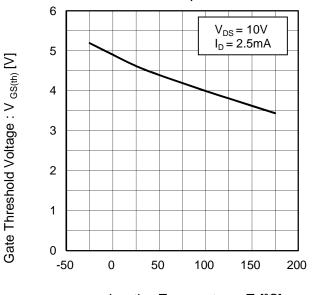
Gate - Source Voltage : V_{GS} [V]

Fig.9 Typical Transfer Characteristics (II)



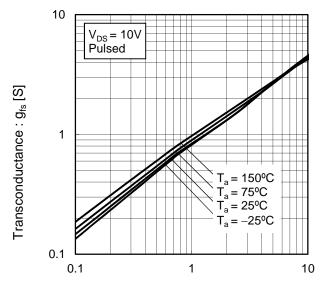
Gate - Source Voltage : V_{GS} [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.11 Transconductance vs. Drain Current



Drain Current : I_D [A]

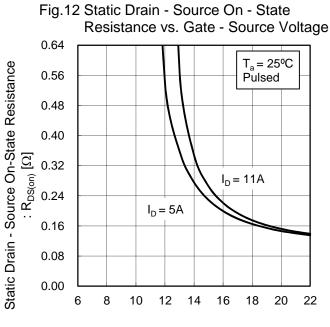
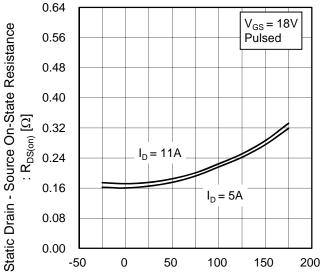
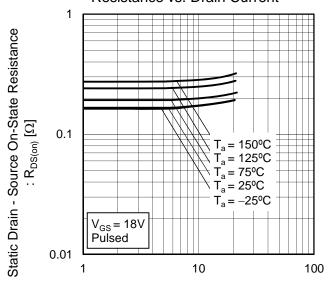


Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature



Gate - Source Voltage : $V_{GS}[V]$ Junction Temperature : $T_i[^{\circ}C]$

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



Drain Current: I_D [A]

 $T_a = 25$ °C f = 1MHz

 $V_{GS} = 0V$

1

0.1

Fig.15 Typical Capacitance
vs. Drain - Source Voltage

10000

1000

Coss

Tr = 25°C

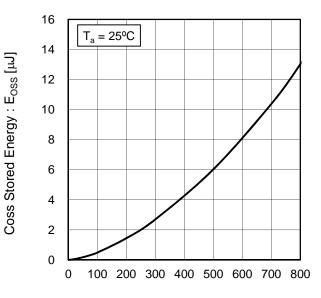
Drain - Source Voltage : V_{DS} [V]

100

1000

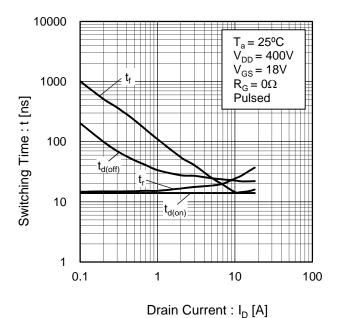
10

Fig.16 Coss Stored Energy



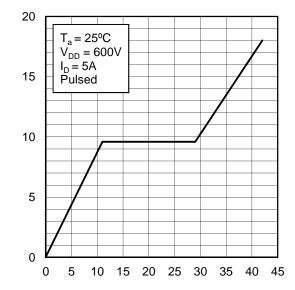
Drain - Source Voltage : V_{DS} [V]

Fig.17 Switching Characteristics

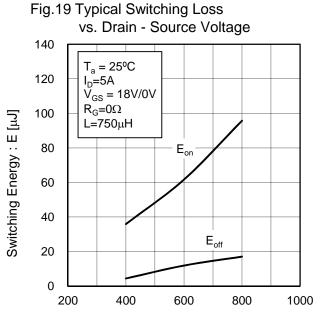


Sate - Source Voltage : V_{GS} [V]

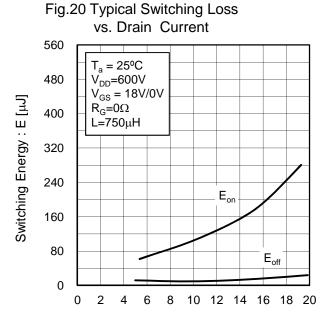
Fig.18 Dynamic Input Characteristics



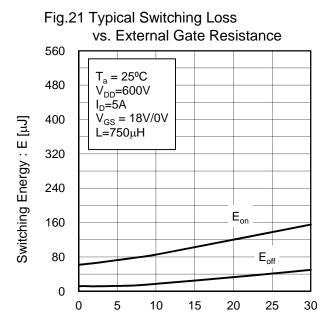
Total Gate Charge : Q_g [nC]



Drain - Source Voltage : V_{DS} [V]

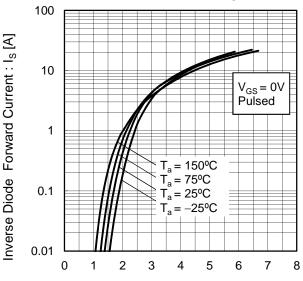


Drain Current : I_D [A]



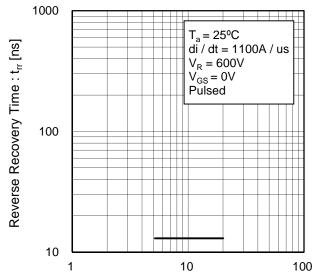
External Gate Resistance : $R_G [\Omega]$

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

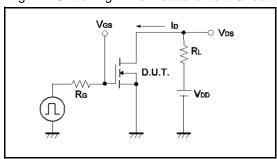


Fig.2-1 Gate Charge Measurement Circuit

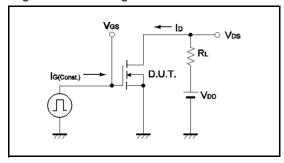


Fig.3-1 Switching Energy Measurement Circuit

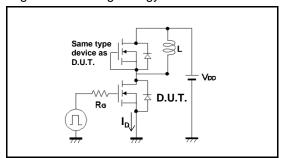


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

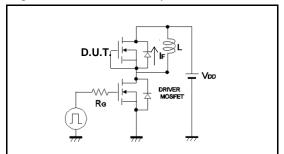


Fig.1-2 Switching Waveforms

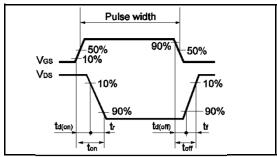


Fig.2-2 Gate Charge Waveform

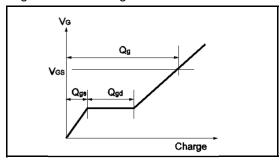
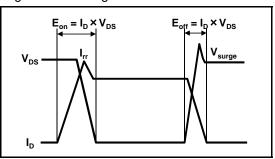
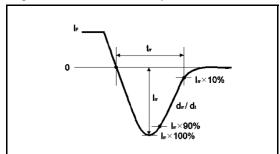


Fig.3-2 Switching Waveforms





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SCT3160KL - Web Page

Distribution Inventory

Part Number	SCT3160KL
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes